

TOSHIBA

2SA1926

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

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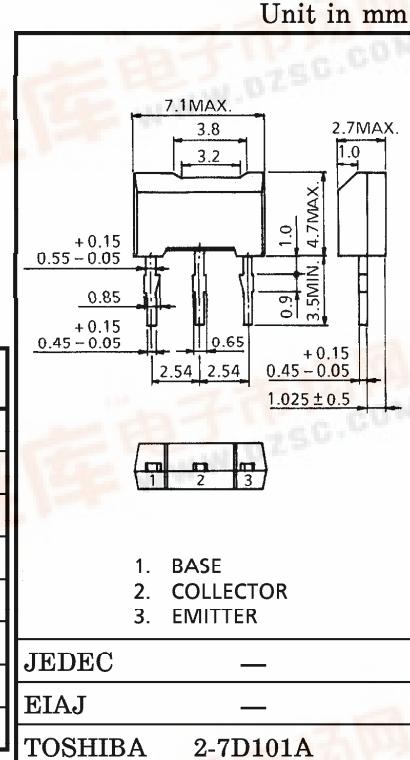
POWER AMPLIFIER APPLICATIONS.

POWER SWITCHING APPLICATIONS.

- Low Collector Saturation Voltage
: $V_{CE}(\text{sat}) = -0.17V$ (Max.) ($I_C = -1A$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-8	V
Collector Current	I_C	-3	A
Base Current	I_B	-1	A
Collector Power Dissipation	P_C	1000	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$



Weight : 0.2g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -80V, I_E = 0$	—	—	-1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -8V, I_C = 0$	—	—	-1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(\text{BR})\text{CEO}}$	$I_C = -10\text{mA}, I_B = 0$	-80	—	—	V
DC Current Gain	$h_{FE}(1)$	$V_{CE} = -2V, I_C = -0.5A$	150	—	400	
	$h_{FE}(2)$	$V_{CE} = -2V, I_C = -1.5A$	40	—	—	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = -1A, I_B = -0.05A$	—	—	-0.17	V
Base-Emitter Saturation Voltage	$V_{BE}(\text{sat})$	$I_C = -1A, I_B = -0.05A$	—	—	-1.2	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -0.5A$	—	80	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1\text{MHz}$	—	45	—	pF

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